





60V PNP SILICON PLANAR MEDIUM POWER TRANSISTOR IN SOT89

Features

- BV_{CEO} > -60V
- High current capability Max Continuous Current I_C = -4.3A
- Low saturation voltage $V_{CE(sat)}$ < -65mV @ I_C = -1A
- Lead Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free, "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT89
- Moisture Sensitivity: Level 1 per J-STD-020
- UL Flammability Rating 94V-0
- Terminals: Matte Tin Finish
- Weight: 0.052 grams (Approximate)

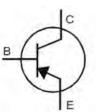
Application

- Emergency lighting circuits
- Motor driving (including DC fans)
- Backlight inverters
- Power switches
- MOSFET gate drivers

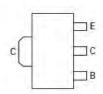
SOT89







Device symbol



Pin-out Top

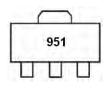
Ordering Information (Note 3 & 4)

Product	Grade	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP2012ZTA	Commercial	951	7	12	1,000
ZXTP2012Z-13R	Commercial	951	7	12	4,000
ZXTP2012ZQTA	Automotive	951	7	12	1,000

Notes:

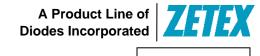
- 1. No purposefully added lead.
- 2. Halogen and Antimony Free. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com 3. For packaging details, go to our website at http://www.diodes.com
- 4. Products with Q-suffix are automotive grade

Marking Information



951 = Product Type Marking Code





ZXTP2012Z

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current (Note 5)	Ic	-4.3	Α
Peak Pulse Current	I _{CM}	-15	Α

Thermal Characteristics @TA = 25°C unless otherwise specified

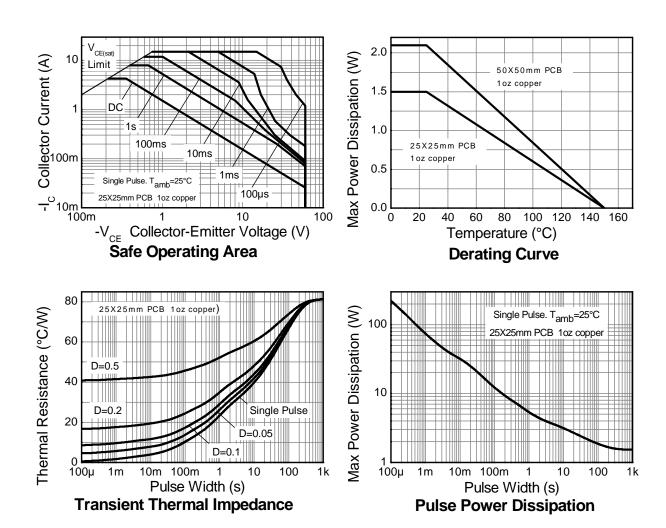
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear derating factor	P _D	1.5 12	W mW/°C
Power Dissipation (Note 6) Linear derating factor	P _D	2.1 16.8	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	83	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	60	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R _{θJL}	3.23	°C/W
Operating and Storage Temperature Range	T _J ,T _{STG}	-55 to +150	°C

Notes:

- 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. 6. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. 7. Thermal resistance from junction to solder-point (on the exposed collector pad).



Thermal Characteristics







ZXTP2012Z

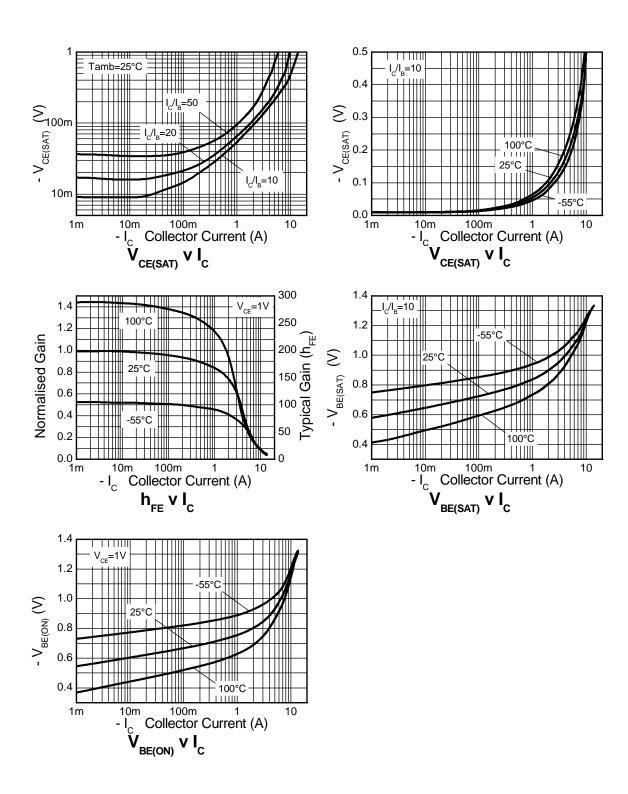
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-100	-120	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Notes 8)	BV _{CER}	-100	-120	-	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Notes 8)	BV _{CEO}	-60	-80	-	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.1	-	V	$I_E = -100 \mu A$
Collector Cutoff Current	I _{CBO}	-	< -1	-20 -500	nA nA	V _{CB} = -80V V _{CB} = -80V, T _A = 100°C
Collector Cutoff Current	l _{CER} R≤1kΩ	-	< -1	-20 -500	nA nA	V _{CB} = -80V V _{CB} = -80V, T _A = 100°C
Emitter Cutoff Current	I _{EBO}	-	< -1	-10	nA	V _{EB} = -6V
DC current transfer Static ratio (Notes 8)	h _{FE}	100 100 45 10	250 200 90 25	300		I _C = -10mA, V _{CE} = -1V I _C = -2A, V _{CE} = -1V I _C = -5A, V _{CE} = -1V I _C = -10A, V _{CE} = -1V
Collector-Emitter Saturation Voltage (Notes 8)	V _{CE(sat)}	-	-14 -50 -75 -160	-20 -65 -110 -215	mV	$I_C = -100$ mA, $I_B = -10$ mA $I_C = -1$ A, $I_B = -100$ mA $I_C = -2$ A, $I_B = -200$ mA $I_C = -5$ A, $I_B = -500$ mA
Base-Emitter Saturation Voltage (Notes 8)	V _{BE(sat)}	-	-950	-1050	mV	$I_{C} = -5A$, $V_{CE} = -1V$
Base-Emitter Turn-on Voltage (Notes 8)	$V_{BE(on)}$	-	-840	-950	mV	$I_C = -5A$, $V_{CE} = -1V$
Transitional Frequency (Notes 8)	f _T	-	120	-	MHz	$I_C = -100 \text{mA}, V_{CE} = -10 \text{V},$ f = 50MHz
Output capacitance	C_obo	-	48	-	pF	$V_{CB} = -10V$, $f = 1MHz$,
Switching Time	t _{ON}	<u> </u>	39	_	ns	$V_{CC} = -10V$, $I_{C} = -1A$,
Owncoming Titlle	toff		370		110	$I_{B1} = I_{B2} = -100 \text{mA}$

Notes: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

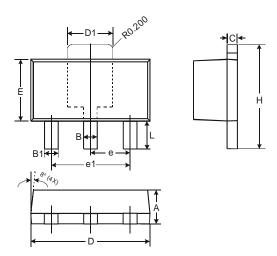


Typical Electrical Characteristics



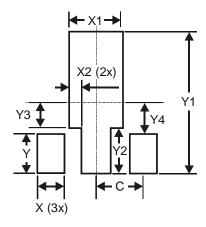


Package Outline Dimensions



SOT89			
Dim	Min	Max	
Α	1.40	1.60	
В	0.44	0.62	
B1	0.35	0.54	
C	0.35	0.43	
D	4.40	4.60	
D1	1.52	1.83	
Е	2.29	2.60	
е	1.50 Typ		
e1	3.00 Typ		
Н	3.94	4.25	
L	0.89	1.20	
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.900
X1	1.733
X2	0.416
Υ	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1.500





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